



AO9926B

Dual N-Channel Enhancement Mode Field Effect Transistor



General Description

The AO9926B/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. This device is suitable for use as a uni-directional or bi-directional load switch.

AO9926B and AO9926BL are electrically identical.

-RoHS Compliant

-AO9926BL is Halogen Free

Features

$V_{DS} (V) = 20V$

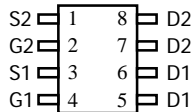
$I_D = 7.6 A (V_{GS} = 10V)$

$R_{DS(ON)} < 23m\Omega (V_{GS} = 10V)$

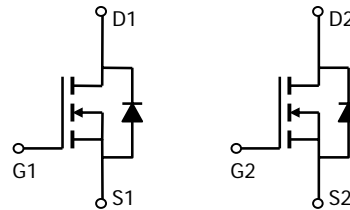
$R_{DS(ON)} < 26m\Omega (V_{GS} = 4.5V)$

$R_{DS(ON)} < 34m\Omega (V_{GS} = 2.5V)$

$R_{DS(ON)} < 52m\Omega (V_{GS} = 1.8V)$



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	7.6
		$T_A=70^\circ C$	6.1
Pulsed Drain Current ^B	I_{DM}	30	A
Power Dissipation ^A	P_D	$T_A=25^\circ C$	2
		$T_A=70^\circ C$	1.28
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	74	110
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	50	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 10\text{V}$			100	nA
BV_{GSO}	Gate-Source Breakdown Voltage	$V_{DS}=0\text{V}$, $I_G=\pm 250\mu\text{A}$	± 12			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.5	0.8	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=7.6\text{A}$ $T_J=125^\circ\text{C}$		18 25	23 30	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=7\text{A}$		21	26	
		$V_{GS}=2.5\text{V}$, $I_D=6\text{A}$		27	34	m Ω
		$V_{GS}=1.8\text{V}$, $I_D=2\text{A}$		38	52	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=7.6\text{A}$		24		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				3.5	A
DYNAMIC PARAMETERS						
C_{ISS}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=10\text{V}$, $f=1\text{MHz}$		630		pF
C_{OSS}	Output Capacitance			164		pF
C_{RSS}	Reverse Transfer Capacitance			137		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.5		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=10\text{V}$, $I_D=7.6\text{A}$		8.8		nC
Q_{gs}	Gate Source Charge			1		nC
Q_{gd}	Gate Drain Charge			3.7		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=5\text{V}$, $V_{DS}=10\text{V}$, $R_L=1.3\Omega$, $R_{GEN}=3\Omega$		5.5		ns
t_r	Turn-On Rise Time			14		ns
$t_{D(off)}$	Turn-Off DelayTime			29		ns
t_f	Turn-Off Fall Time			10.2		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=7.6\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		15.2		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=7.6\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		6.3		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current and power rating is based on the $\leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

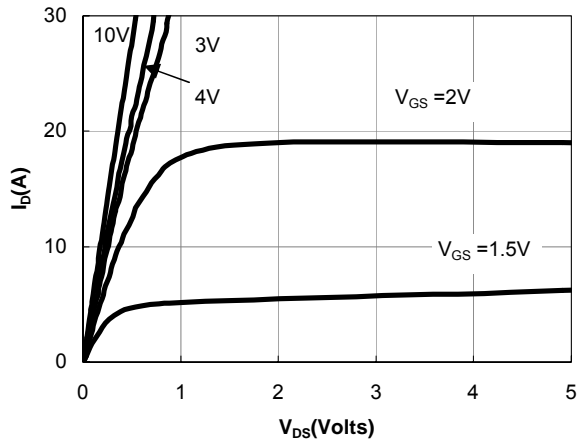


Figure 1: On-Regions Characteristics

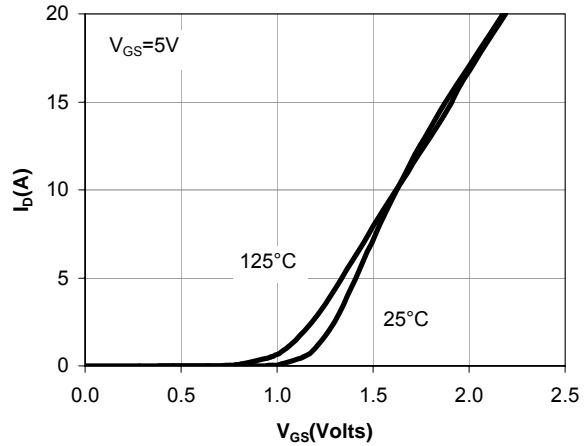


Figure 2: Transfer Characteristics

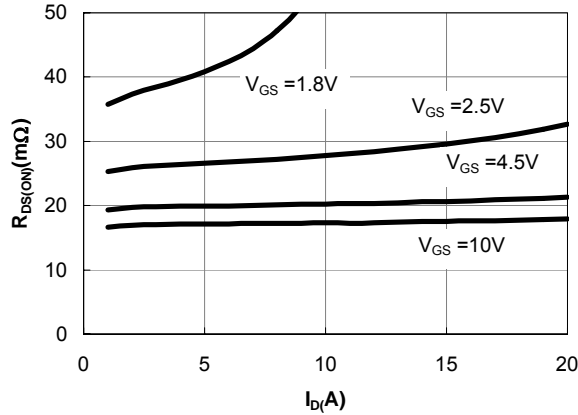


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

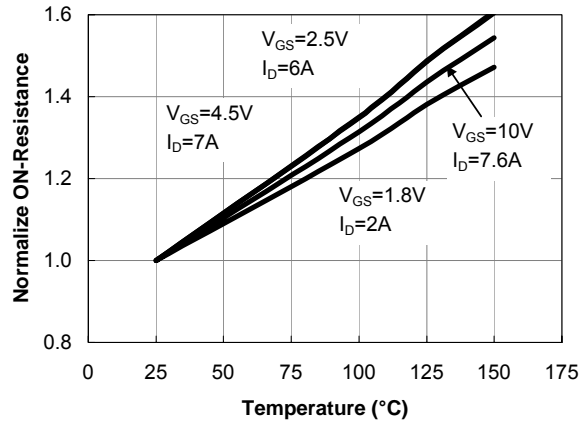


Figure 4: On-Resistance vs. Junction Temperature

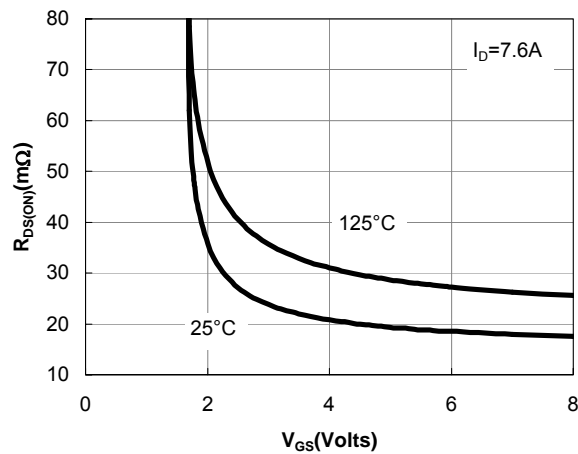


Figure 5: On-Resistance vs. Gate-Source Voltage

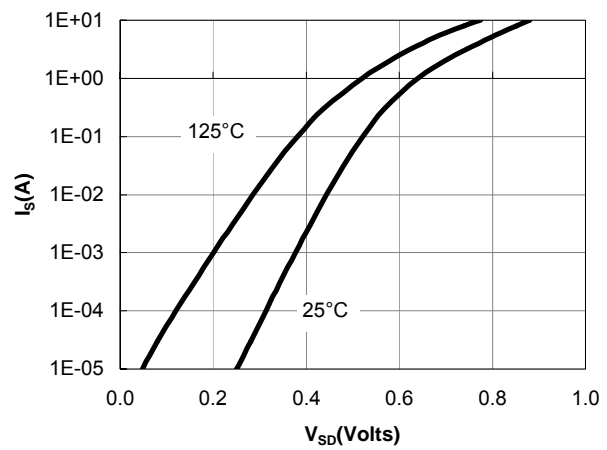


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

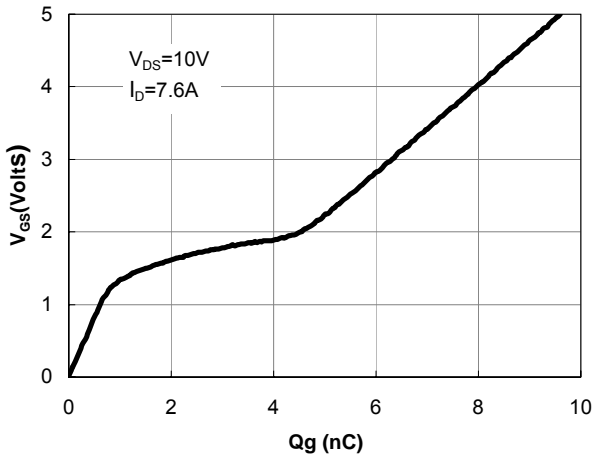


Figure 7: Gate-Charge Characteristics

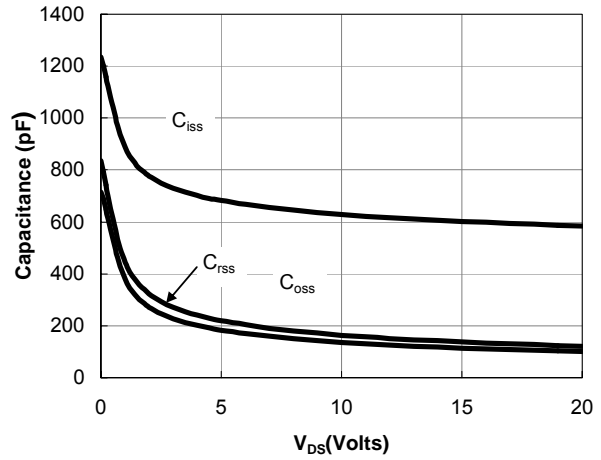


Figure 8: Capacitance Characteristics

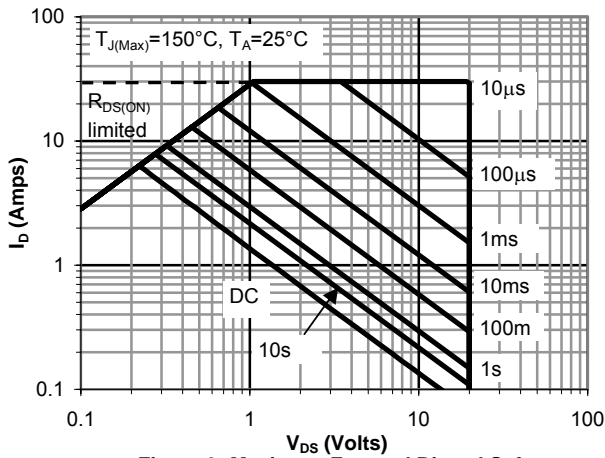


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

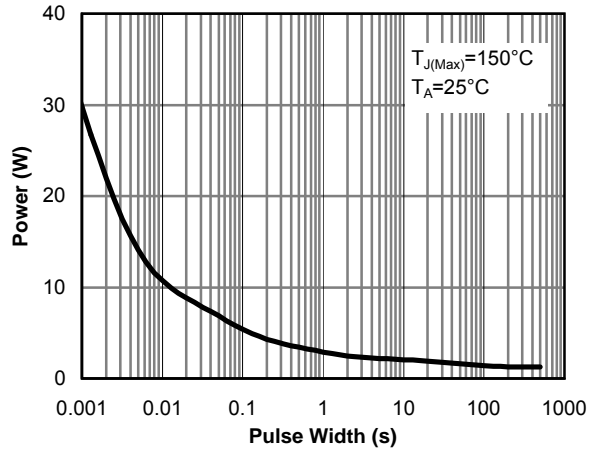


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

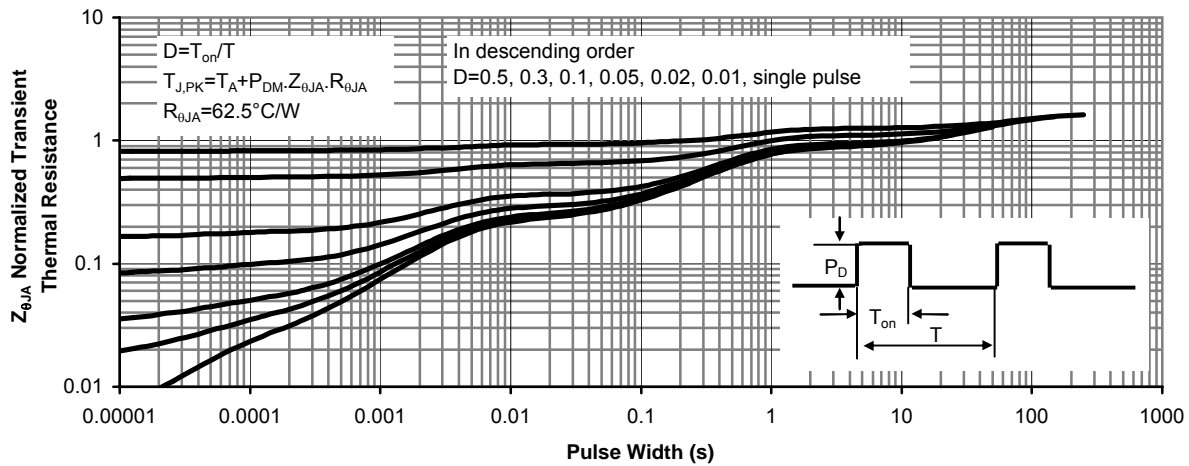


Figure 11: Normalized Maximum Transient Thermal Impedance